

Mingmin Huang

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	A Carrier-Storage-Enhanced Superjunction IGBT With Ultralow Loss and On-State Voltage. IEEE Electron Device Letters, 2018, 39, 264-267.	3.9	39
2	Recrystallization effects of swift heavy 209 Bi ions irradiation on electrical degradation in 4H-SiC Schottky barrier diode. Nuclear Instruments & Methods in Physics Research B, 2017, 401, 51-55.	1.4	16
3	A Vertical Superjunction MOSFET With n-Si and p-3C-SiC Pillars. IEEE Transactions on Electron Devices, 2019, 66, 3922-3928.	3.0	10
4	A Multi-epi Superjunction MOSFET With a Lightly Doped MOS-Channel Diode for Improving Reverse Recovery. IEEE Transactions on Electron Devices, 2021, 68, 2401-2407.	3.0	9
5	Carrier-storage-enhanced superjunction IGBT with n-Si and p-3C-SiC pillars. Electronics Letters, 2019, 55, 1353-1355.	1.0	7
6	Investigation of 4H-SiC Schottky barrier diodes irradiated with 6 MeV Au ions at low temperature. Nuclear Instruments & Methods in Physics Research B, 2021, 494-495, 53-58.	1.4	5
7	Recrystallization effects in GeV Bi ion implanted 4H-SiC Schottky barrier diode investigated by cross-sectional Micro-Raman spectroscopy. Nuclear Instruments & Methods in Physics Research B, 2020, 478, 5-10.	1.4	4
8	Low-loss reverse blocking IGBT with PNM structure and trench collectors. Electronics Letters, 2019, 55, 350-351.	1.0	3
9	Snapback-free reverse conducting IGBT with p-poly trench collectors. Electronics Letters, 2020, 56, 153-155.	1.0	3
10	Semi-superjunction IGBT with a relatively high-resistance p-top region for low on-state and turn-off losses. Superlattices and Microstructures, 2021, 158, 107025.	3.1	2
11	Superjunction MOSFET with Trench Schottky Contact and Embedded High-k Insulator for Excellent Reverse Recovery. , 2021, , .		2
12	Semi-superjunction IGBT with floating p-pillar and p-ring for low losses and high breakdown voltage. , 2021, , .		1
13	Superjunction MOSFET with a trench contact on partly relatively lightly doped P-pillar for excellent reverse recovery. Semiconductor Science and Technology, 2021, 36, 105002.	2.0	0
14	Snapback-free reverse conducting IGBT with p-float and n-ring surrounding trench collector. Electronics Letters, 2020, 56, 1337-1340.	1.0	0
15	A Novel Power PiN Diode with p-type Schottky Anode and Trench Oxide for Improving Reverse Recovery. , 2021, , .		0